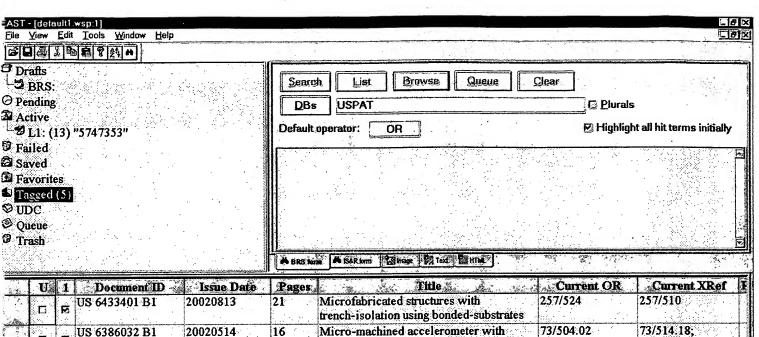


1	, D	,D	US 20020190319 A1	20021219	14	Method for microfabricating structures using silicon-on-insulator material	257/347	
2	D.	G.	US 20020187422 A1		8	compositions as hardmask layer		430/272.1; 430/280.1;
3	Б	Б	US 6581640 B1	20030624	15		137/833	216/41; 216/56;
1	П	Б	US 6540203 B1	20030401	44	Pilot operated microvalve device	251/26	251/129.01; 251/129.07
5	Б	G	US 6533554 B1	20030318	11	Thermal transpiration pump	417/207	417/48; 417/53
5	П	П	US 6503692 B2	20030107	7	Antireflective silicon-containing compositions as hardmask layer	430/310	
7	П	Г	US 6494804 B1	20021217	12	Microvalve for electronically controlled transmission	475/127	137/625.6; 475/138
8	П	Б	US 6420088 B1	20020716	6	Antireflective silicon-containing compositions as hardmask layer	430/272.1	430/270.1; 430/950;
9	Г	Б	US 6420084 B1	20020716	9	Mask-making using resist having SIO bond-containing polymer	430/270.1	430/277.1; 430/278.1;
10 📝	П	С	US 6402301 B1	20020611	12	Ink jet printheads and methods therefor	347/63	
11	· C	Б	US 6392313 B1	20020521	89	Microturbomachinery	290/52	257/414; 310/40MM;
12.	.	Б	US 6342430 B1	20020129	17	Trench isolation for micromechanical devices	438/424	257/E21.546; 438/421;
13	П	Б	US 6239473 B1	20010529	17	Trench isolation for micromechanical devices	257/419	257/254; 257/417;
14	Б	ß	US 6133615 A	20001017	15	Photodiode arrays having minimized cross-talk between diodes	257/446	257/292; 257/466;
15	С	Б	US 5932940 A	19990803	92	Microturbomachinery	310/40MM	257/414; 257/415;
16	Б	Г	US 5865938 A	19990202	10	Wafer chuck for inducing an electrical bias across wafer heterojunctions	156/345.51	
17	П	P	US 5637189 A	19970610	10	Dry etch process control using electrically biased stop junctions	438/466	216/67; 216/79;
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34	U	1	Document ID	Issue Date	Pages	Title	AS Current OR	Current XRef F
	Б	Ø	US 6433401 B1	20020813	21	Microfabricated structures with trench-isolation using bonded-substrates	257/524	257/510
	D	R	US 6386032 B1	20020514	16	Micro-machined accelerometer with improved transfer characteristics	73/504.02	73/514.18; 73/514.32
	П	ᅜ	US 6313529 B1	20011106	19	Bump bonding and sealing a semiconductor device with solder	257/724	257/778; 257/780;
	ı	R	US 6291875 B1	20010918	15	Microfabricated structures with electrical isolation and interconnections	257/622	257/499
	П	P	US 6184052 B1	20010206	7	Process for manufacturing high-sensitivity capacitive and resonant integrated sensors,		257/E21.552; 257/E21.573;

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